

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)
)
Shoji SETA, et al.) Group Art Unit: *Not Yet Assigned*
)
Cont. of Application No.: 09/739,905) Examiner: *Not Yet Assigned*
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Filed: Herewith)
)
For: DRY ETCHING METHOD AND)
SEMICONDUCTOR DEVICE)
MANUFACTURING METHOD)

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

PRELIMINARY AMENDMENT

Prior to the examination of the above application, please amend this application as follows:

IN THE ABSTRACT:

Please replace the current Abstract with the Substitute Abstract attached on a separate page. The full text of the Abstract in clean form is as follows:

--A dry etching method comprises sequentially laminating a first insulating layer containing carbon and a second insulating layer containing carbon on a substrate, patterning the second insulating layer to form a mask; forming grooves in the first insulating layer by etching the first insulating layer with the second insulating layer used as a mask such that each of the grooves has a side surface and a bottom surface in the first insulating layer; and removing the